

**Description**

The SX4N20MSI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = 200V$   $I_D = 4.2A$

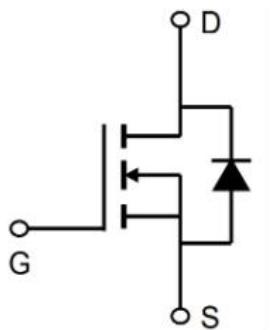
$R_{DS(ON)} < 580m\Omega @ V_{GS}=10V$

**Application**

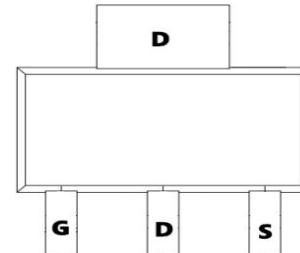
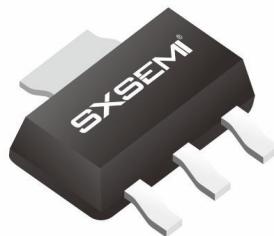
Automotive lighting

Load switch

Uninterruptible power supply



SOT-223-3L

**Absolute Maximum Ratings (TC=25°C unless otherwise noted)**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	200	V
V <sub>GS</sub>	Gate-Source Voltage	$\pm 20$	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Drain Current, V <sub>GS</sub> @ 10V	4.2	A
I <sub>D</sub> @T <sub>c</sub> =100°C	Drain Current, V <sub>GS</sub> @ 10V	2.8	A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	10	A
P <sub>D</sub> @T <sub>c</sub> =25°C	Total Power Dissipation	2	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.1	W
T <sub>TSG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJA</sub>	Maximum Thermal Resistance, Junctionambient	85	°C/W
R <sub>θJC</sub>	Maximum Thermal Resistance, Junction-case	3.9	°C/W

**Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	200	230	---	V
R <sub>DSON</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =1A	---	450	580	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =1A	---	680	850	mΩ
V <sub>GTH</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	2	2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =1A	---	10	---	S
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =160V , V <sub>GS</sub> =10V , I <sub>D</sub> =1A	---	15	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.0	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	5.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time		---	22	---	ns
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =100V , V <sub>GS</sub> =10V , R <sub>G</sub> =3 , I <sub>D</sub> =1A	---	34	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	45	---	
T <sub>f</sub>	Fall Time		---	11	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , F=1MHz	---	900	---	pF
C <sub>oss</sub>	Output Capacitance		---	130	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	4.6	---	
I <sub>s</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	1	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>s</sub> =1A , T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =1A , di/dt=100A/μs , T <sub>J</sub> =25°C	---	85	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	257	---	nC

**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

## Typical Characteristics

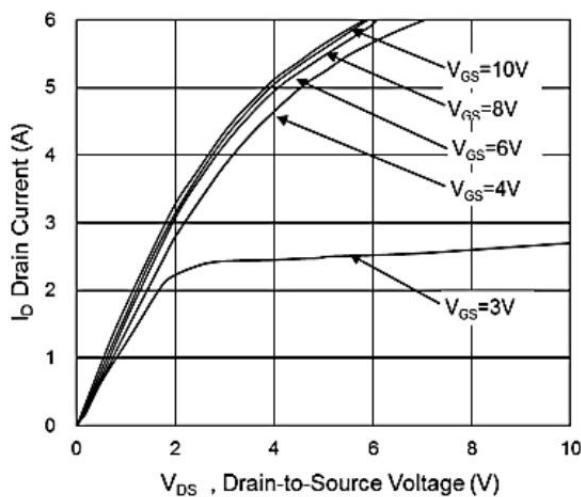


Fig.1 Typical Output Characteristics

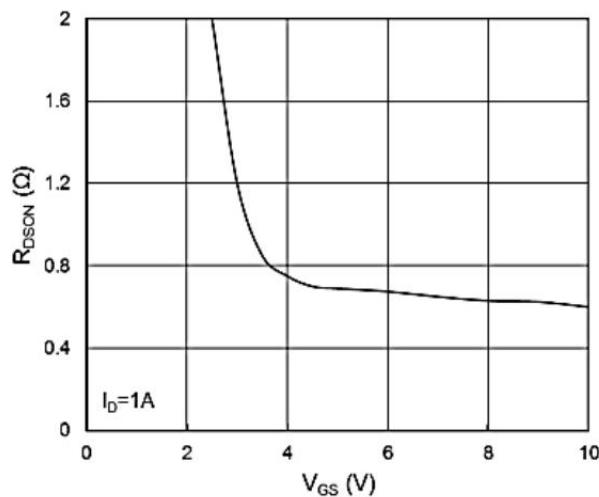


Fig.2 On-Resistance vs. G-S Voltage

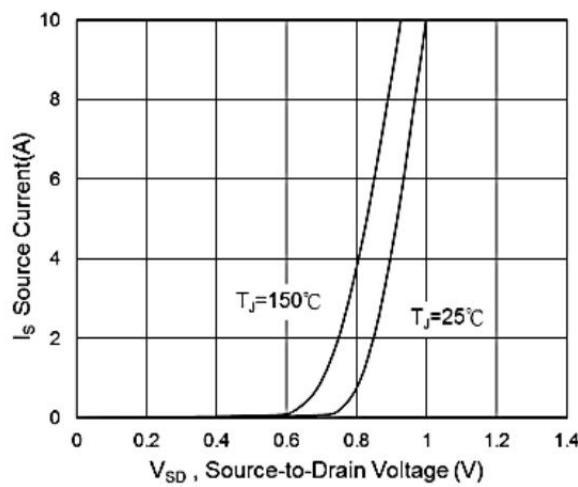


Fig.3 Forward Characteristics of Reverse

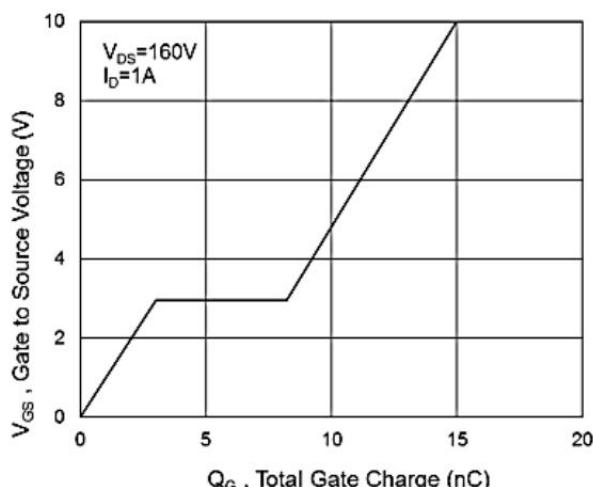


Fig.4 Gate-Charge Characteristics

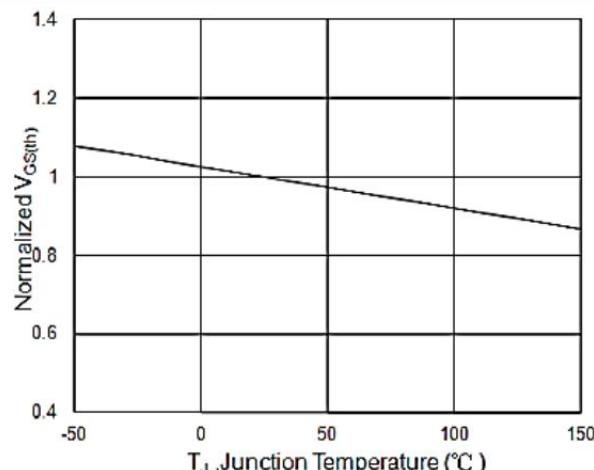


Fig.5  $V_{GS(th)}$  vs.  $T_J$

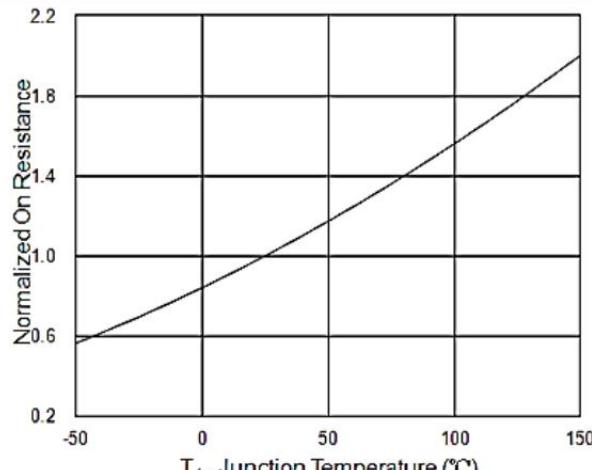


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

## Typical Characteristics

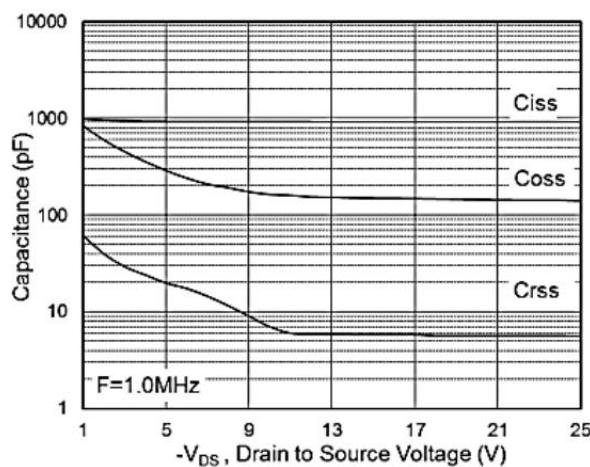


Fig.7 Capacitance

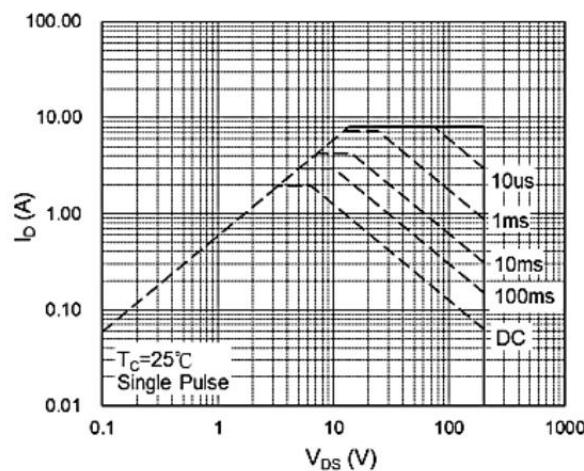


Fig.8 Safe Operating Area

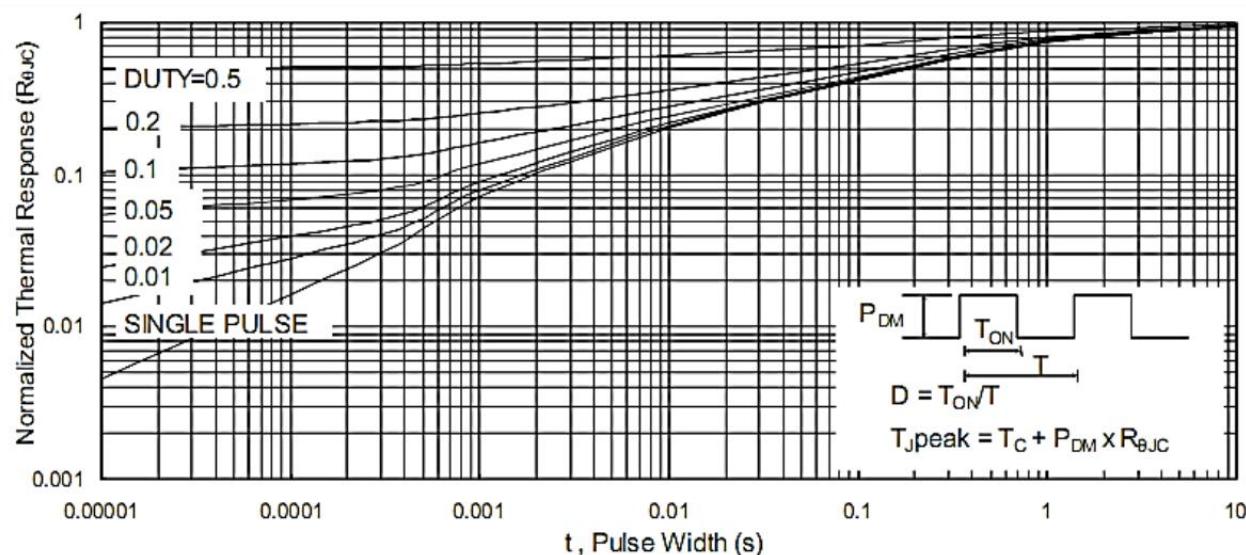


Fig.9 Normalized Maximum Transient Thermal Impedance

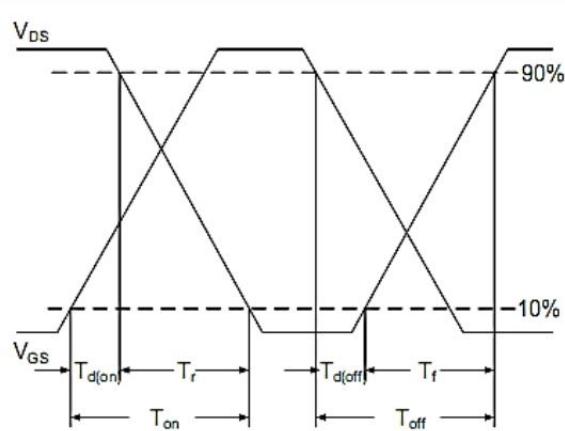


Fig.10 Switching Time Waveform

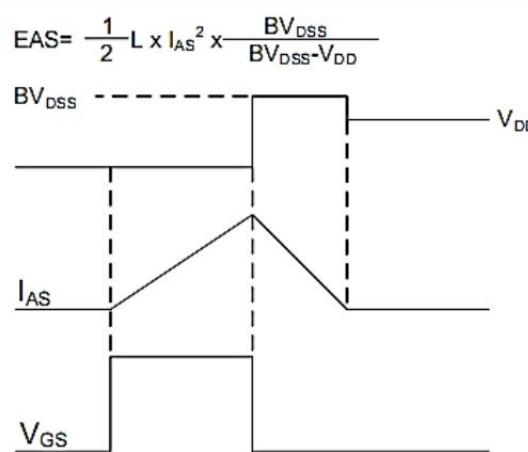
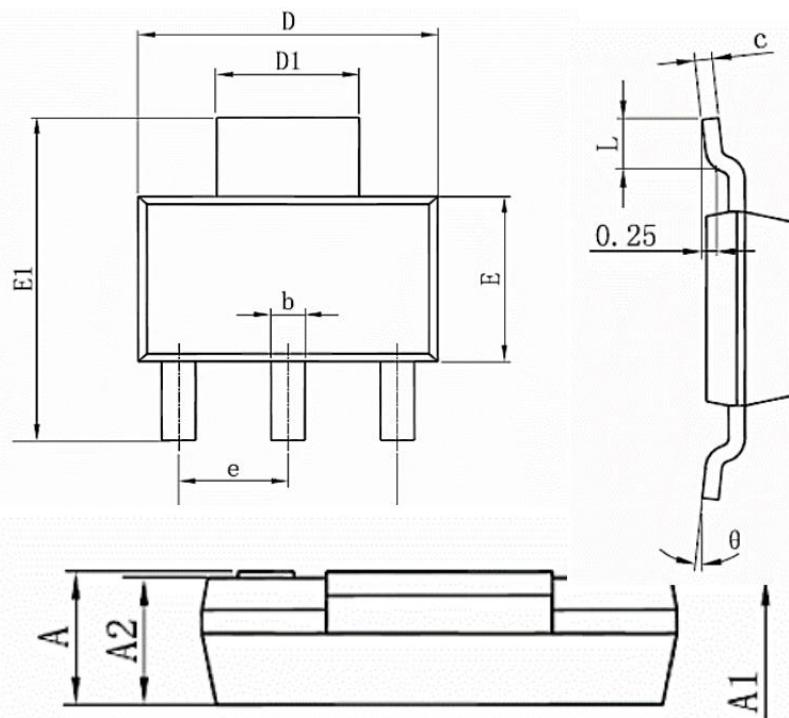


Fig.11 Unclamped Inductive Switching Waveform

## Package Mechanical Data:SOT223-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.52	1.8	0.06	0.049
A1	0.000	0.100	0.000	0.004
A2	1.5	1.7	0.059	0.045
b	0.66	0.82	0.026	0.032
c	0.25	0.35	0.010	0.014
D	6.2	6.4	0.244	0.252
D1	2.9	3.1	0.114	0.122
E	3.3	3.7	0.130	0.146
E1	6.83	7.07	0.269	0.278
e	2.300(BSC)		0.037(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.15	0.035	0.045
θ	0°	10°	0°	10°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT223-3L		3000